

P@DJLP JL PCBQ pba l k L dbkq i Pbj f l kar d op r kfr b absf b abpfdk d efsb il t OAPLK& il t d φ e adb) c pqpt fq eikd ka bu biibkq s i k eb e o φφφ p Qeb efde S φ pbdbp fp pntb f iiv I mofj fmab d oeefde pvpφj p t fp d φ adskd sl iq db dφ φoφ k . - S

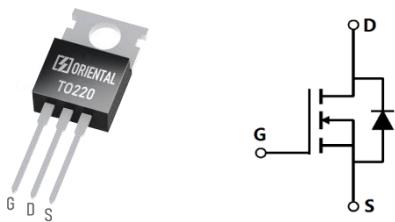
- Il t OAPLK& CL J
- Buqbj biv il t pt fq eikd il pp
- Bu biibkqpq fify ka rkfd q fq
- C pqpt fq eikd ka pl qφb l sbv



- Pt fq eba j l ab ml t bopr mmiv
- Jl d oadsbo
- φφφ mφ qφ k
- A@A@ l ksba o
- Solar inverter
- RMP ka bkbølv fksba o

Parameter	Value	Unit
V _{DS, min} @ T _{j(max)}	80	V
I _{D, pulse}	840	A
R _{DS(ON), max} @ V _{GS} =10V	2.6	j
Q _g	148.1	nC

Product Name	Package	Marking
SFG280N08PF	TO220	SFG280N08P



Absolute Maximum Ratings at $T_j=25$ @unless otherwise noted

Parameter

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C _{iss}		10486		pF	V _{GS} =0 V, V _{DS} =50 V, f = 1 MHz
Output capacitance	C _{oss}		2022		pF	
Reverse transfer capacitance	C _{rss}		19.9		pF	
Turn-on delay time	t _{d(on)}		39.5		ns	V _{GS} =10 V, V _{DS} =50 V, R _G =2.2 Ω I _D =25 A
Rise time	t _r		27.5		ns	
Turn-off delay time	t _{d(off)}		73.3		ns	
Fall time	t _f		16.1		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q _g		148.1		nC	V _{GS} =10 V, V _{DS} =50 V, I _D =25 A
Gate-source charge	Q _{gs}		36.5		nC	
Gate-drain charge	Q _{gd}		35.9		nC	
Gate plateau voltage	V _{plateau}		4.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V _{SD}			1.3	V	I _S =20 A, V _{GS} =0 V
Reverse recovery time	t _{rr}		112		ns	V _R =50 V, I _S =25 A, afq . -- , p
Reverse recovery charge	Q _{rr}		477.5		nC	
Peak reverse recovery current	I _{rrm}		6.9		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of R_G is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
- 5) V_{DD}=50 V, V_{GS}=10 V, L=0.3 mH, starting T_j=25 °C.

Electrical Characteristics Diagrams

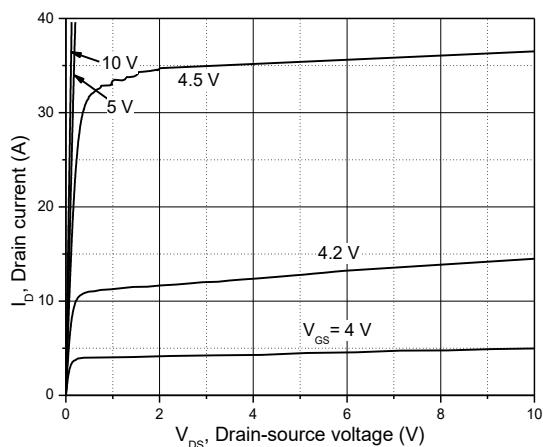


Figure 1. Typ. output characteristics

Figure 2. Typ. transfer characteristics

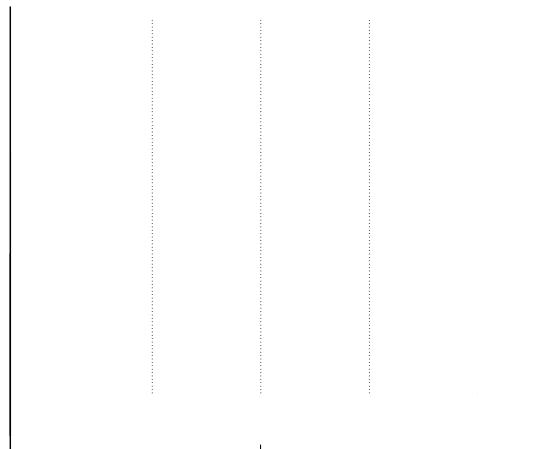


Figure 3. Typ. capacitances

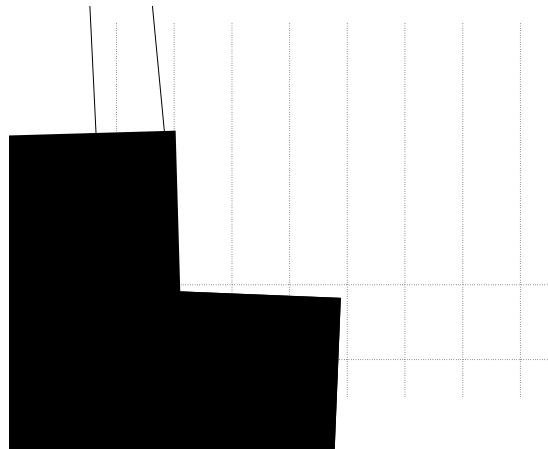


Figure 4. Typ. gate charge

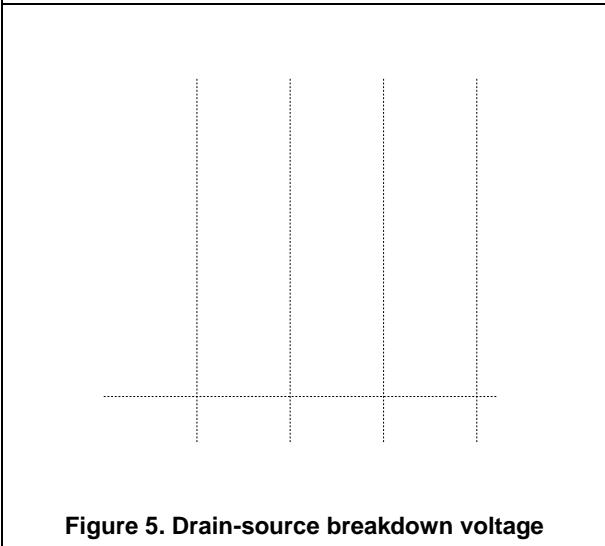


Figure 5. Drain-source breakdown voltage

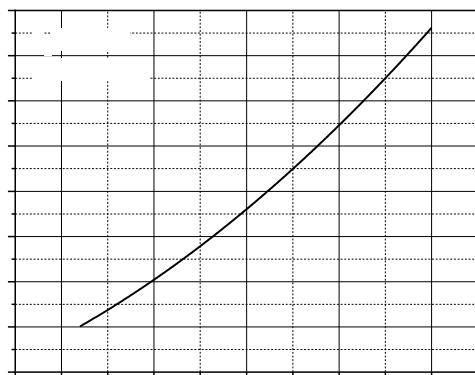
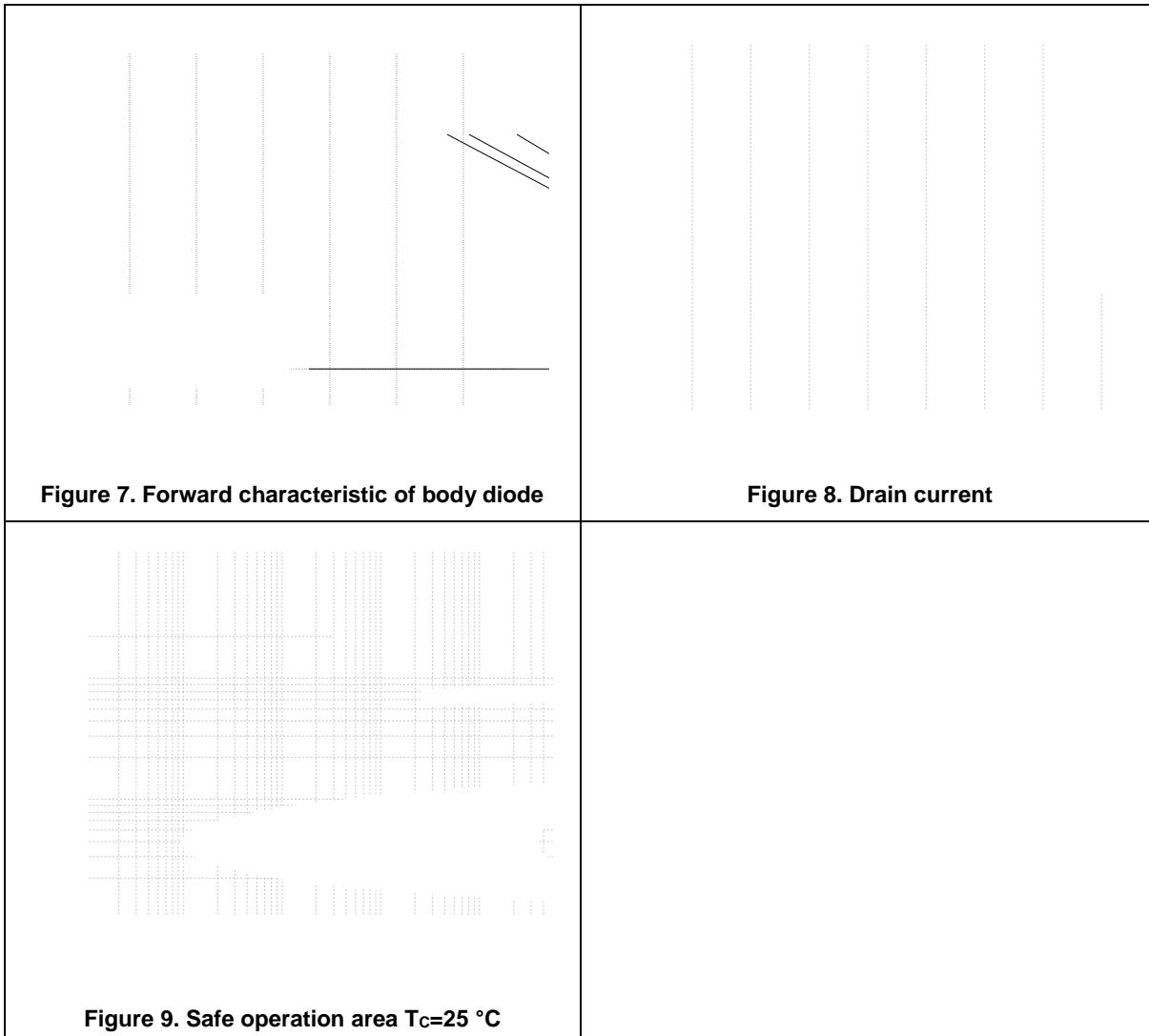


Figure 6. Drain-source on-state resistance



Test circuits and waveforms

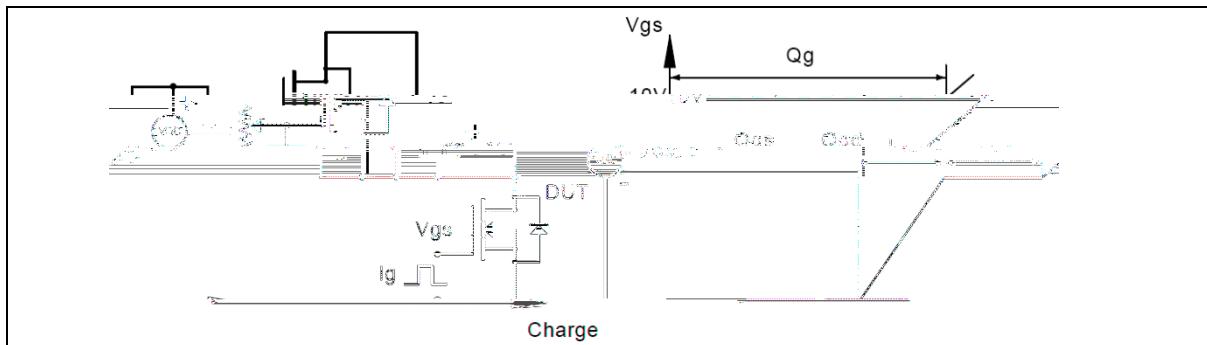


Figure 1. Gate charge test circuit & waveform

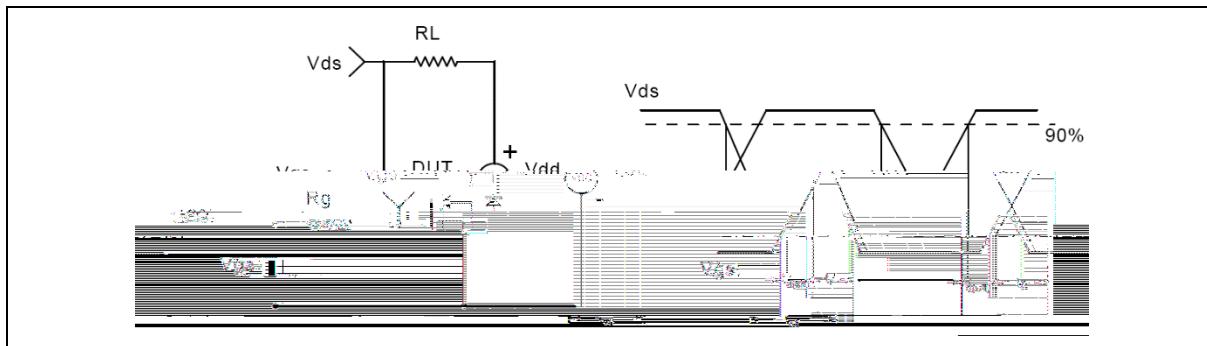


Figure 2. Switching time test circuit & waveform

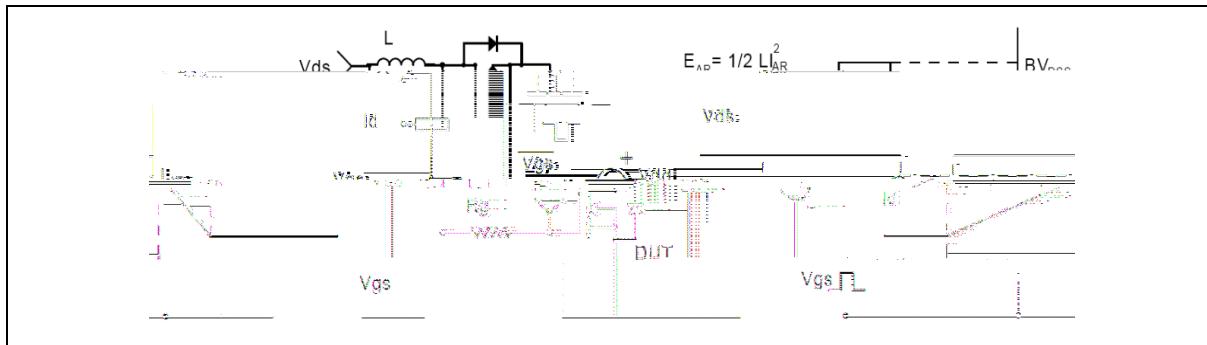


Figure 3. Unclamped inductive switching (UIS) test circuit & waveform

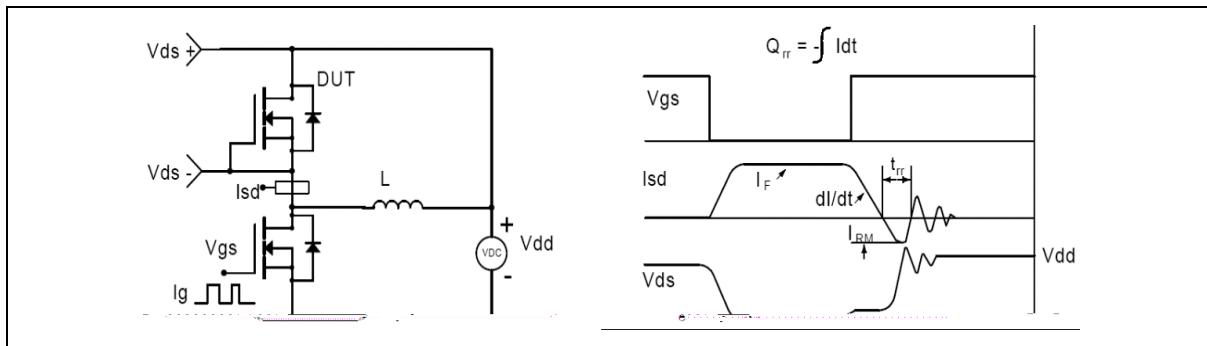
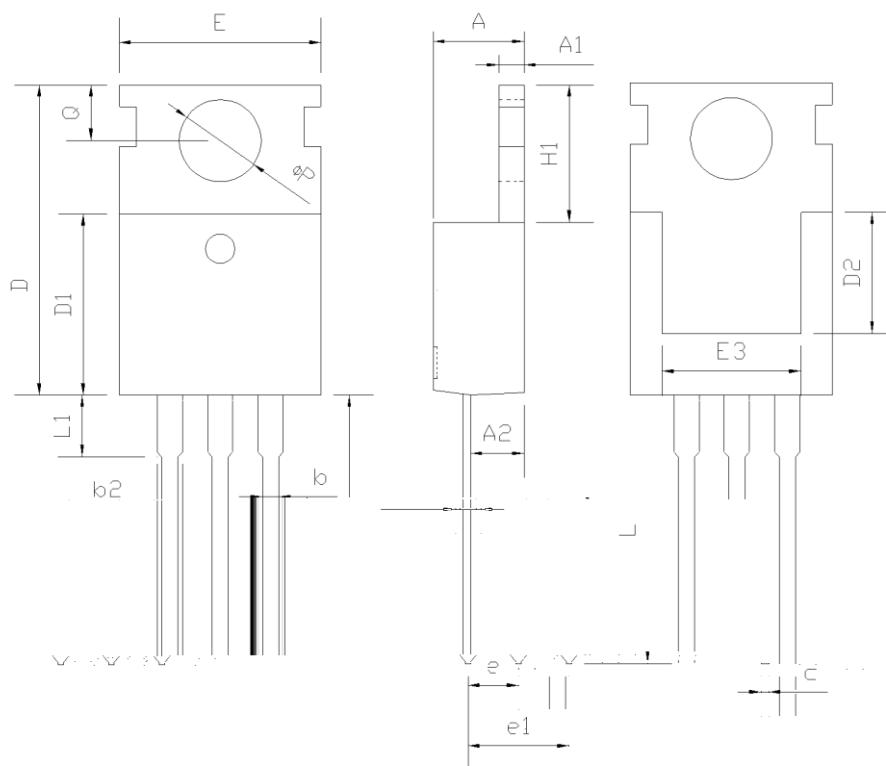


Figure 4. Diode reverse recovery test circuit & waveform

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
M	3.40	3.60	3.80
Q	2.60	2.80	3.00

Version 1: TO220-C package outline dimension

Ordering Information

Package Type	Units/Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220-C	50	20	1000	6	6000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG280N08PF	TO220	yes	yes	yes

Qeb fkd qj q k dfsbk fk qfb al rj bkqpe ii fk kl bsbkq b ddb oaba p dr o kfb l c
 I kfq kp l o e o ffbqf p T fq dfrn b qd kv bu j mfp l o efkf dfsbk ebdk) kv
 qmf i s irbp pq ffa ebdk ka,l o kv fkd qj q k ddb oafkd qfb mmif q k l cfb absf b)
 L dbkq i Pbj f l kar q oebw v afp i fj p kv ka ii t o kfbp ka if fidbp l c kv hfka)
 fk irafkd t fqp r qifj fq q k)t o kfbp l ckl k-fkakdbj bkql c fkphiib q i m o m o y ofdeq l c
 kv qfbm o y

A o a fbo fkd qj q k l k f ekl il dv) abifbav ffbj p ka I kfq kp ka mf bp) mfp pb
 I kq qfb L dbkq i Pbj f l kar q op ibp dfrn bpkq qfbp [t t t l dbkq ipbj f l j &](#)

